

**AMENDMENT**

**Claim Amendments**

1. (canceled)
2. (canceled)
3. (canceled)
4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (original) A method of controlling the breakdown voltage of a snapback device, comprising  
controlling doping levels of an isolation region by using a perforated mask during doping of the isolation region.
11. (original) A method of claim 10, further comprising annealing the device.
12. (original) A method of claim 10, further comprising exposing the device to one or more predefined elevated temperatures for predefined times.
13. (original) A method of increasing the breakdown voltage of a snapback device comprising  
forming an isolation layer between active regions and substrate of the device, wherein the isolation layer includes forming spotted implants.
14. (original) A method of claim 13, wherein the spotted implants are formed by making use of a mask with intermittent openings.
15. (original) A method of claim 13, wherein the spotted implants are provided before one or both of an epitaxial layer being grown and high diffusion drive taking place.
16. (original) A method of claim 13, wherein the snapback device is an ESD protection device.
17. (original) A method of claim 13, further comprising annealing the device.

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18. (original) A method of claim 13, further comprising exposing the device to one or more predefined elevated temperatures for predefined times.